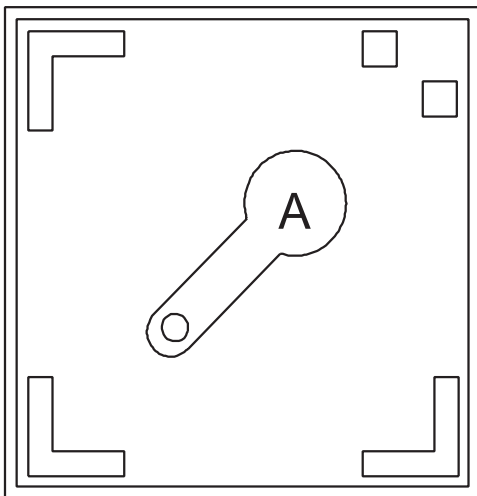


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.5 X 9.5 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	2.5 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 13,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

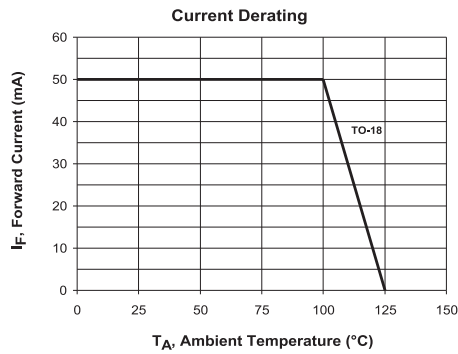
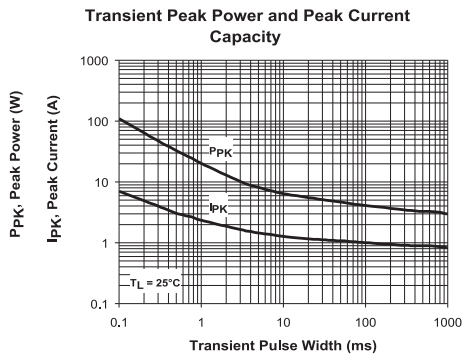
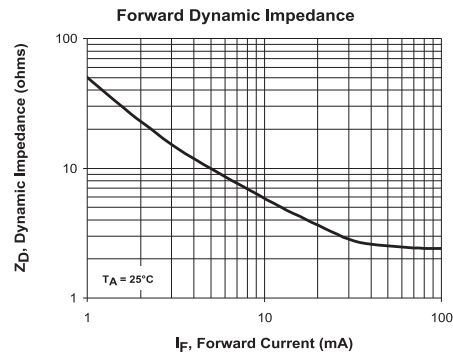
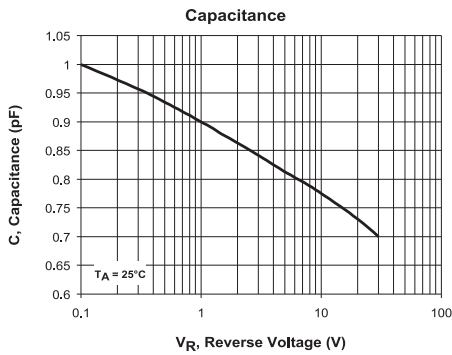
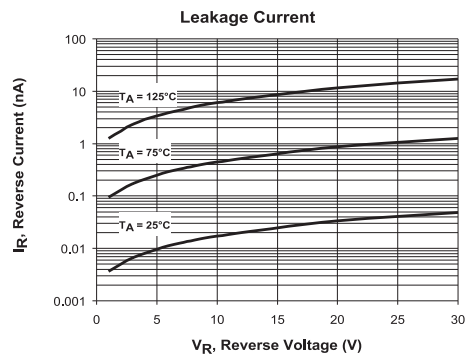
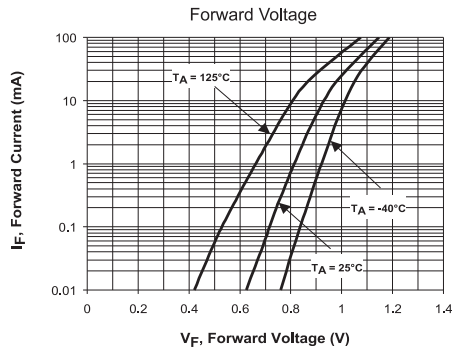
125,200

PRINCIPAL DEVICE TYPES

BAV45

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R1 (1-August 2002)



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